

Lindsay Hussey

List of Publications by Year in descending order

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Version: 2024-02-01

15
papers

625
citations

840585

11
h-index

1058333

14
g-index

15
all docs

15
docs citations

15
times ranked

704
citing authors

#	ARTICLE	IF	CITATIONS
1	The role of surface kinetics on composition and quality of AlGaN. Journal of Crystal Growth, 2016, 451, 65-71.	0.7	112
2	Advantages and limitations of UV optoelectronics on AlN substrates. , 2015, , .		0
3	Fermi level control of compensating point defects during metalorganic chemical vapor deposition growth of Si-doped AlGaN. Applied Physics Letters, 2014, 105, 222101.	1.5	47
4	Exciton transitions and oxygen as a donor in <i>m</i> -plane AlN homoepitaxial films. Journal of Applied Physics, 2014, 115, .	1.1	20
5	Homoepitaxial AlN thin films deposited on <i>m</i> -plane (11 $\bar{2}$ 00) AlN substrates by metalorganic chemical vapor deposition. Journal of Applied Physics, 2014, 116, 133517.	1.1	30
6	Stimulated emission and optical gain in AlGaN heterostructures grown on bulk AlN substrates. Journal of Applied Physics, 2014, 115, .	1.1	56
7	Sapphire decomposition and inversion domains in N-polar aluminum nitride. Applied Physics Letters, 2014, 104, .	1.5	29
8	The effect of polarity and surface states on the Fermi level at III-nitride surfaces. Journal of Applied Physics, 2014, 116, .	1.1	75
9	Properties of AlN based lateral polarity structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 261-264.	0.8	11
10	Direct Observation of the Polarity Control Mechanism in Aluminum Nitride Grown on Sapphire by Aberration Corrected Scanning Transmission Electron Microscopy. Microscopy and Microanalysis, 2014, 20, 162-163.	0.2	2
11	Lasing and longitudinal cavity modes in photo-pumped deep ultraviolet AlGaN heterostructures. Applied Physics Letters, 2013, 102, .	1.5	104
12	Polarity control and growth of lateral polarity structures in AlN. Applied Physics Letters, 2013, 102, .	1.5	60
13	Lateral epitaxial overgrowth of nitrogen polar GaN on smooth nitrogen polar GaN templates by metalorganic chemical vapor deposition. Journal of Applied Physics, 2012, 112, .	1.1	3
14	On the strain in n-type GaN. Applied Physics Letters, 2011, 99, 141916.	1.5	25
15	Strain in Si doped GaN and the Fermi level effect. Applied Physics Letters, 2011, 98, 202101.	1.5	51